



STN2NF10

N-channel 100V - 0.23Ω - 2.4A - SOT-223
STripFET™ II Power MOSFET

Features

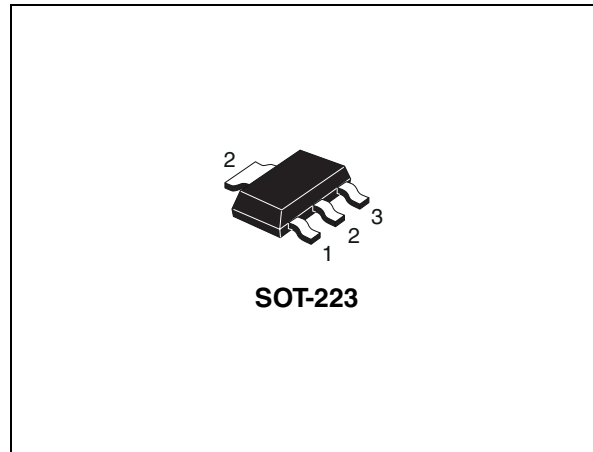
Type	V _{DSS}	R _{DS(on)}	I _D
STN2NF10	100V	< 0.26Ω	2.4A

Description

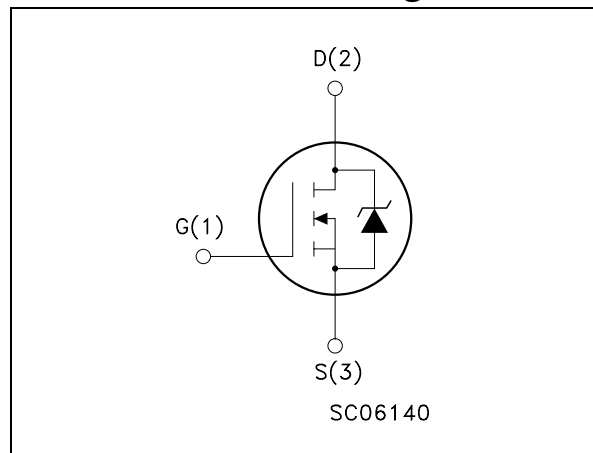
This Power MOSFET is the latest development of STMicroelectronics unique “single feature size” strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Application

- Switching application
 - DC-DC converters



Internal schematic diagram



Order code

Part number	Marking	Package	Packaging
STN2NF10	N2NF10	SOT-223	Tape & reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuit	9
4	Package mechanical data	10
5	Revision history	12

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS}=0$)	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	2.4	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	1.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	17	A
	Derating factor	0.026	W/ $^\circ\text{C}$
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25^\circ\text{C}$	3.3	W
$E_{AS}^{(3)}$	Single pulse avalanche energy	200	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	30	V/ns
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. This value is rated according to $R_{thj-amb}$, $t \leq 10\text{sec}$
3. $I_{AS} = 2.4\text{A}$, $V_{DD} = 30\text{V}$, $R_g = 4.7\Omega$, starting $T_j = 25^\circ\text{C}$
4. $I_{SD} \leq 6\text{A}$, $di/dt \leq 500\text{A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb	38	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(2)}$	Thermal resistance junction-amb	62.5	$^\circ\text{C}/\text{W}$

1. When mounted on 1inch² FR-4 board, 2 oz. Cu, ($t < 10\text{sec}$)
2. When mounted on 1inch² FR-4 board, 2 oz. Cu, ($t > 10\text{sec}$)

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$ $V_{DS} = 30V, T_c = 125^{\circ}C$			1 10 1	μA μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 1.2A$		0.23	0.26	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward transconductance	$V_{DS} = 15V, I_D = 1.2A$		2.5		S
C_{iss}	Input capacitance	$V_{DS} = 25V, f = 1MHz, V_{GS} = 0$		280		pF
C_{oss}	Output capacitance			45		pF
C_{rss}	Reverse transfer capacitance			20		pF
Q_g	Total gate charge	$V_{DD} = 80V, I_D = 6A$		10	14	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10V$		2.5		nC
Q_{gd}	Gate-drain charge	(see Figure 15)		4		nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD}=50V$, $I_D = 2.4A$ $V_{GS} = 10V$, $R_G=4.7\Omega$ (see Figure 14)		6 10		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD}=50V$, $I_D = 2.4A$ $V_{GS} = 10V$, $R_G=4.7\Omega$ (see Figure 14)		20 3		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				2.4 17	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}= 2.4A$, $V_{GS}=0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}= 6A$, $V_{DD}=10V$ $di/dt=100A/\mu s$, $T_j=150^\circ C$ (see Figure 19)		70 175 5		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

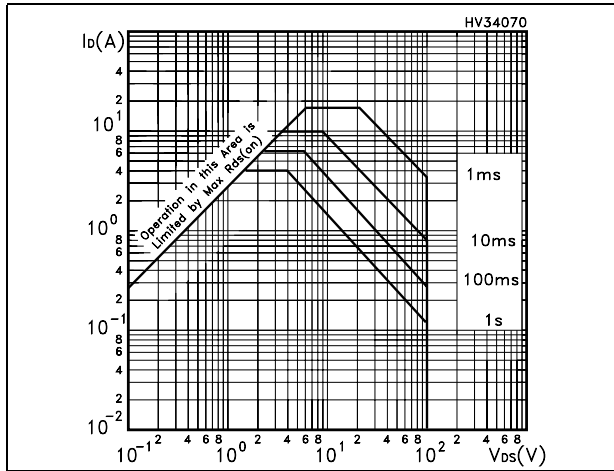


Figure 2. Thermal impedance

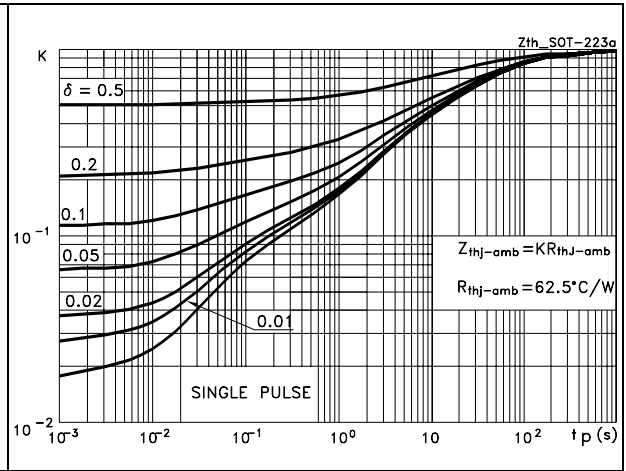


Figure 3. Output characteristics

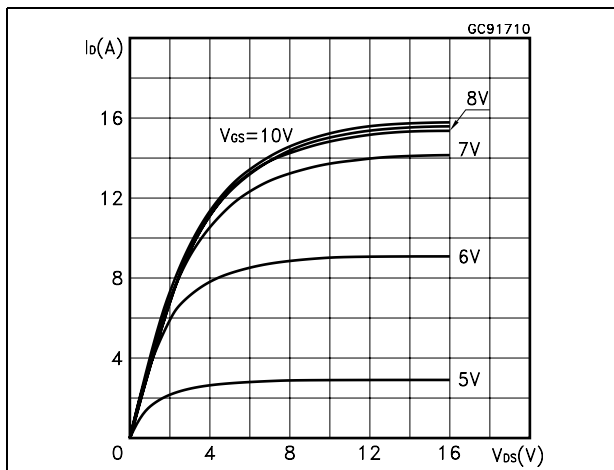


Figure 4. Transfer characteristics

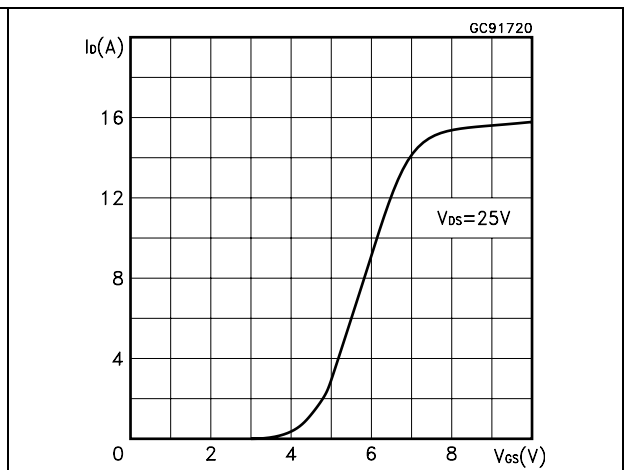


Figure 5. Transconductance

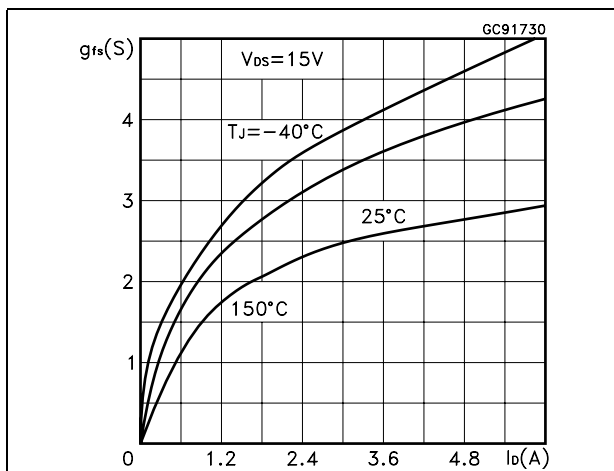


Figure 6. Static drain-source on resistance

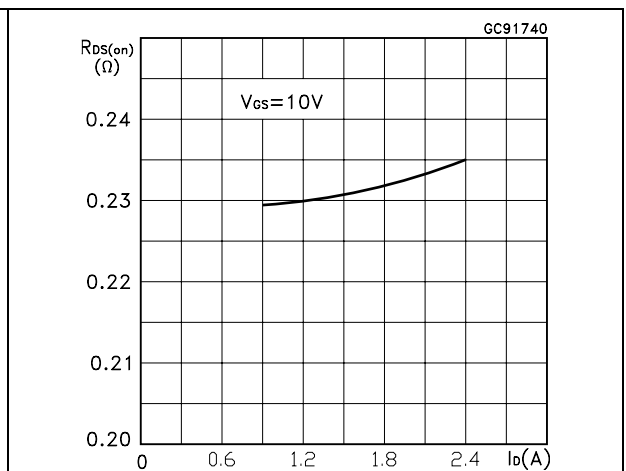


Figure 7. Gate charge vs. gate-source voltage

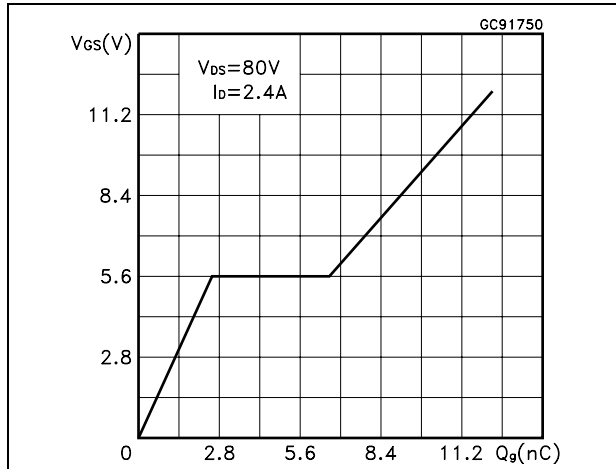


Figure 8. Capacitance variations

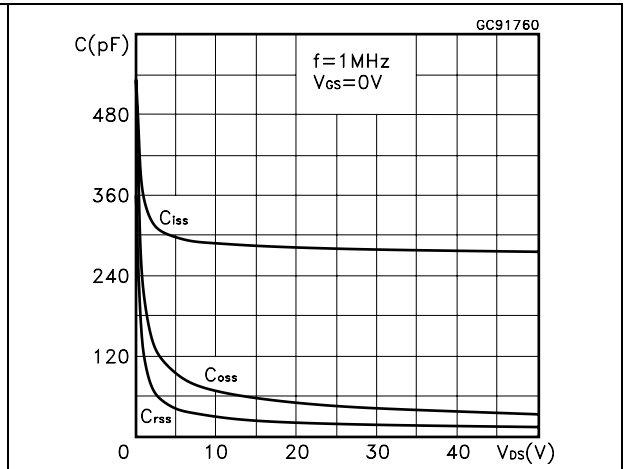


Figure 9. Normalized gate threshold voltage vs. temperature

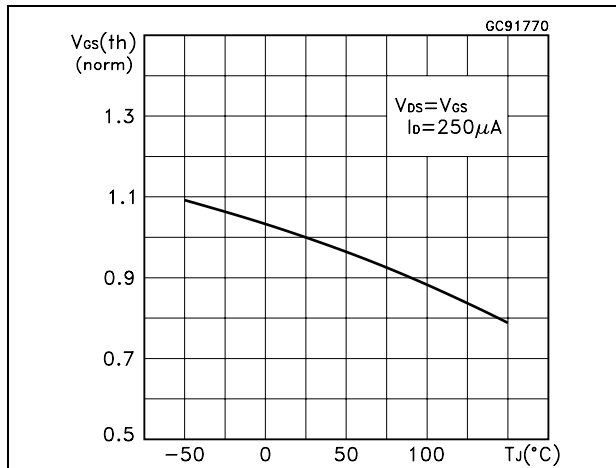


Figure 10. Normalized on resistance vs. temperature

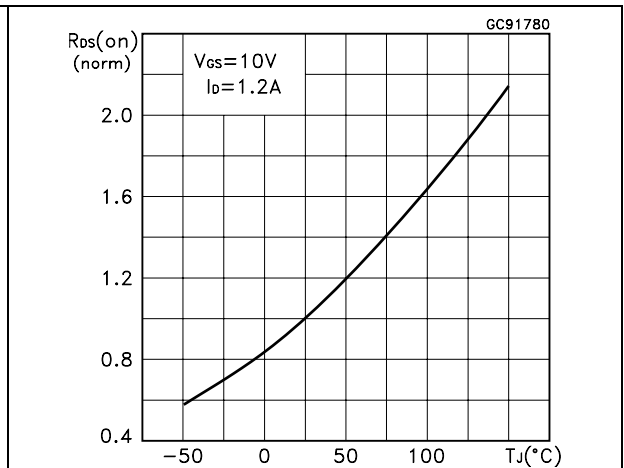


Figure 11. Source-drain diode forward characteristics

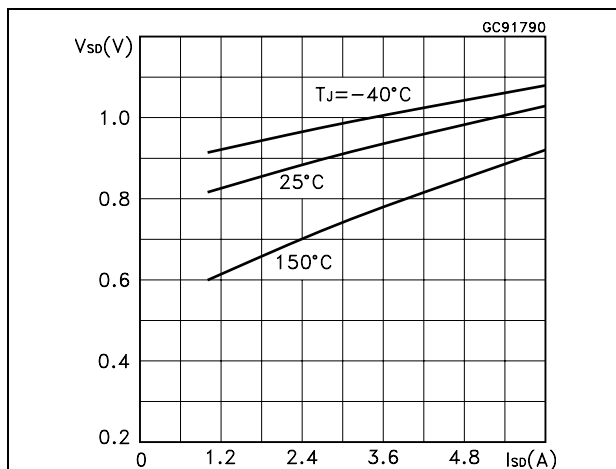


Figure 12. Normalized BV_{DSS} vs. temperature

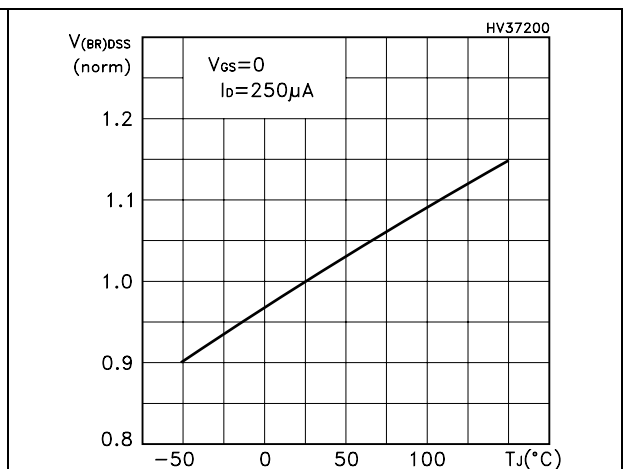
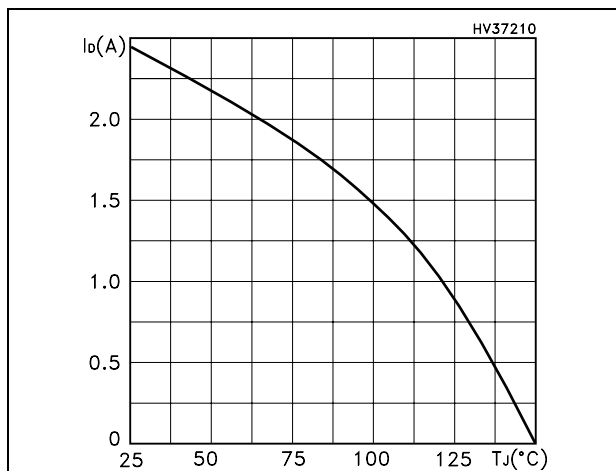


Figure 13. Max drain current vs. temperature



3 Test circuit

Figure 14. Switching times test circuit for resistive load

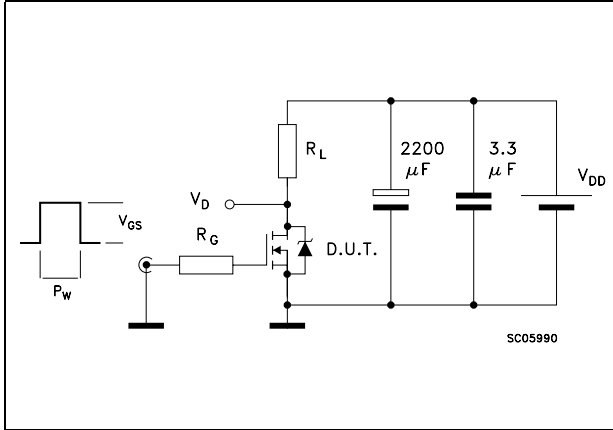


Figure 15. Gate charge test circuit

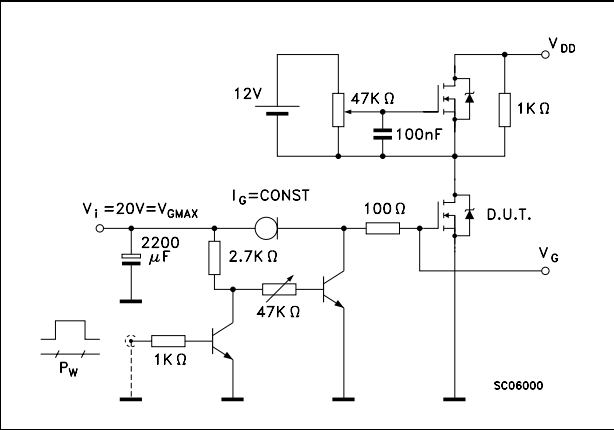


Figure 16. Test circuit for inductive load switching and diode recovery times

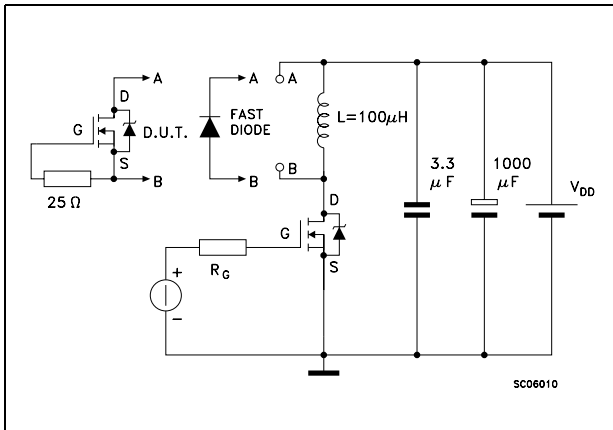


Figure 17. Unclamped inductive load test circuit

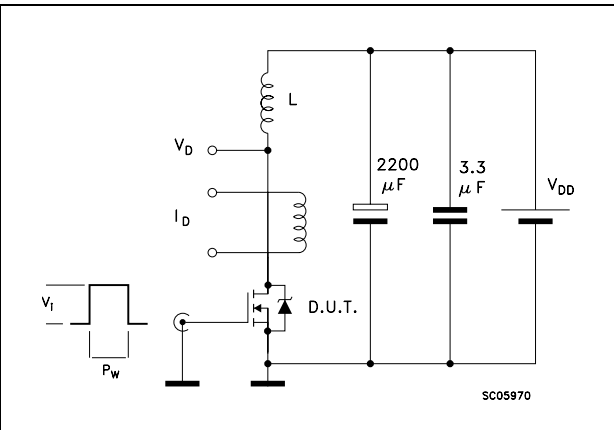


Figure 18. Unclamped inductive waveform

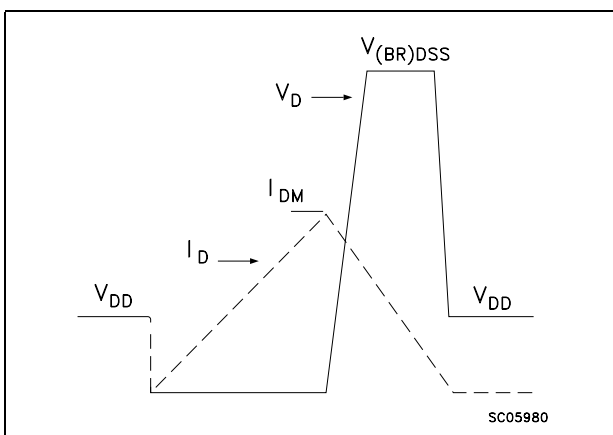
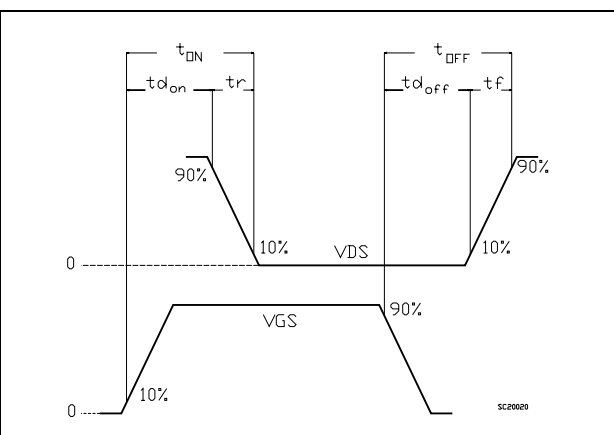


Figure 19. Switching time waveform

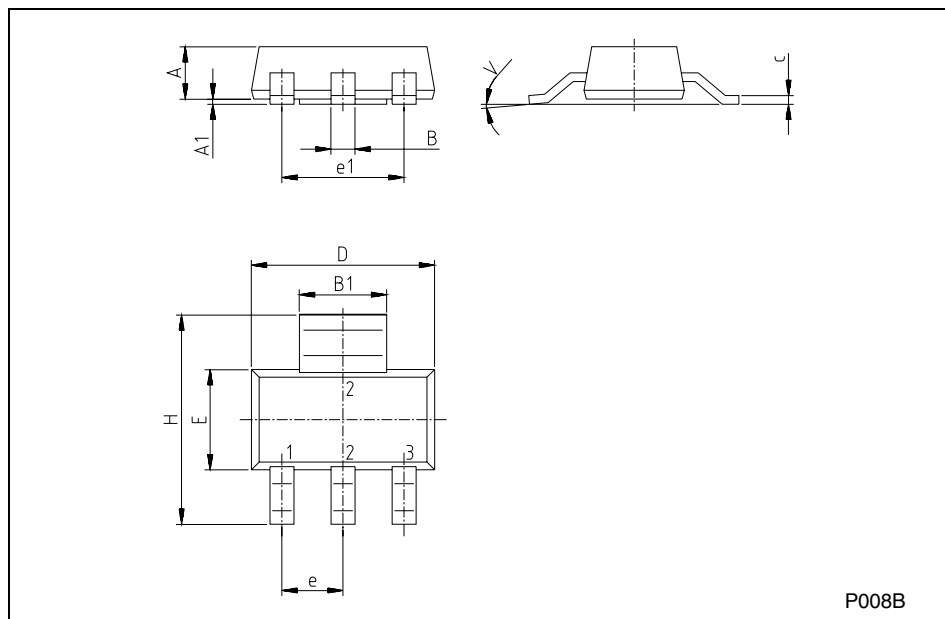


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



5 Revision history

Table 7. Revision history

Date	Revision	Changes
14-Sep-2006	4	The document has been reformatted
29-Mar-2007	5	<i>Figure 1</i> has been updated
04-Apr-2007	6	New test condition for I_{DSS} on <i>Table 3</i>

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com